Abstracts

Infrared temperature characterization of high power RF devices

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Infrared microscopy measurement methodology has been refined to measure high power RF device temperatures accurately at high frequencies (1 GHz, 2+ GHz). Special difficulties due to translucent nature of Si are resolved. The methodology is applied to practical Si bipolar, Si LDMOS and GaAs RF power devices. Product thermal performance characterization method is established. Methodology is also applied in product development efforts.

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